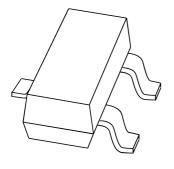
DISCRETE SEMICONDUCTORS

DATA SHEET 25-05885



BAT17Schottky barrier diode

Product data sheet Supersedes data of 1999 May 26 2003 Mar 25



Schottky barrier diode

BAT17

FEATURES

- Low forward voltage
- Small SMD package
- · Low capacitance.

APPLICATIONS

- UHF mixer
- · Sampling circuits
- Modulators
- Phase detection.

DESCRIPTION

Planar Schottky barrier diode in a small SOT23 plastic SMD package.

MARKING

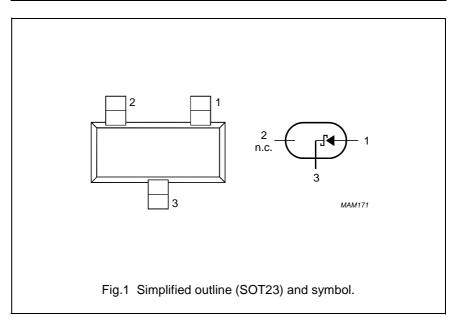
TYPE NUMBER	MARKING CODE ⁽¹⁾		
BAT17	A3*		

Note

- * = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 - * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	anode
2	not connected
3	cathode



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_R	continuous reverse voltage	_	4	V
I _F	continuous forward current	_	30	mA
T _{stg}	storage temperature	-65	+150	°C
Tj	junction temperature	_	100	°C

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V _F	forward voltage	see Fig.2		
		I _F = 0.1 mA	350	mV
		I _F = 1 mA	450	mV
		I _F = 10 mA	600	mV
I _R	reverse current	V _R = 3 V; see Fig.3	0.25	μΑ
		$V_R = 3 \text{ V}; T_{amb} = 60 \text{ °C}; \text{ see Fig.3}$	1.25	μΑ
r_D	diode forward resistance	f = 1 kHz; I _F = 5 mA	15	Ω
C _d	diode capacitance	f = 1 MHz; V _R = 0; see Fig.4	1	pF
F	noise figure	f = 900 MHz; note 1	8	dB

Note

1. The local oscillator is adjusted for a diode current of 2 mA. IF amplifier noise F_{if} = 1.5 dB; f = 35 MHz.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

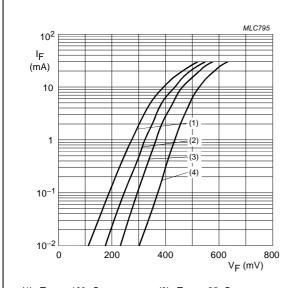
1. Refer to SOT23 standard mounting conditions.

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GRAPHICAL DATA



- (1) $T_{amb} = 100 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.
- (2) $T_{amb} = 60 \, ^{\circ}C$.
- (4) $T_{amb} = -40 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.

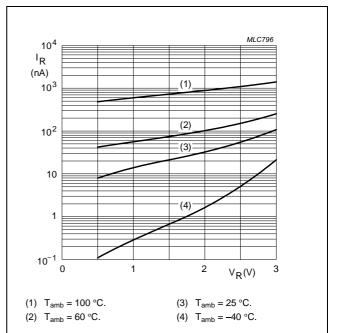
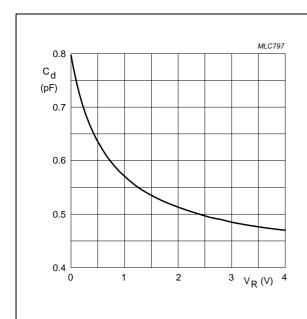


Fig.3 Reverse current as a function of reverse voltage; typical values.



f = 1 MHz; $T_{amb} = 25 \, ^{\circ}\text{C}$.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

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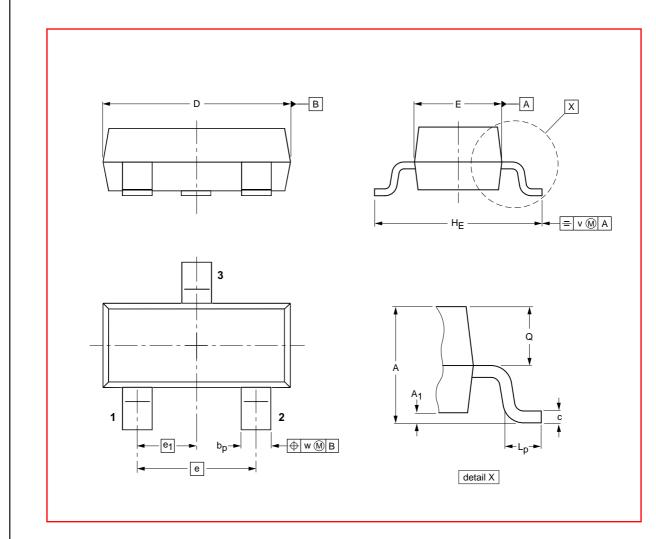
Schottky barrier diode

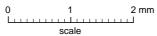
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23





DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁ max.	bp	С	D	E	е	e ₁	HE	Lp	ø	٧	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT23		TO-236AB				-97-02-28- 99-09-13

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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2003 Mar 25

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors. No changes were made to the content, except for the legal definitions and disclaimers.

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